WILLAS

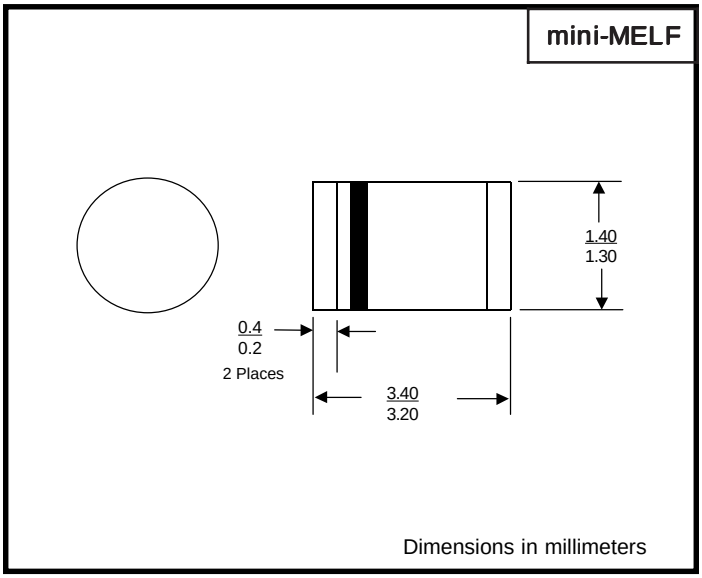
MM4150

1N4150 mini-MELF SIGNAL DIODE

Pb Free Product

Absolute Maximum Ratings (Ta=25◦C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VR	50	V
Reverse Recovery Time	trr	4	ns
Power Dissipation	P_{tot}	500	mW
Forward Current	IF	200	mA
Junction Temp.	Tj	-65 to 200	◦C
Storage Temp.	Tstg	-65 to 200	◦C



Mechanical Data

Items	Materials
Package	Mini MELF
Case	Hermetically sealed glass
Lead/Finish	Double stud/Solder Plating
Chip	Glass Passivated

Electrical Characteristics (Ta=25◦C)

Ratings	Symbol	Ratings	Unit
Minimum Breakdown Voltage @IR= 100uA	BV	75	V
Peak Forward Surge Current PW< 1sec.	IFsurge	500	mA
Maximum Forward Voltage IF= 200mA	VF	1.0	V
Maximum Reverse Current VR= 50V	IR	100	nA
Maximum Junction Capacitance VR= 0, f= 1 MHz	Cj	4	pF
Maximum Reverse Recovery Time IF= 10mA, VR= 6V, IRR= 1mA, RL= 100Ω	trr	4	ns
Maximum Thermal Resistance	RθJA	0.35	◦C/mW